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Responsible committee: EPL/47 Semiconductors

Interested committees:

Title: Draft BS IEC 62373-1 Ed.1.0 Semiconductor devices - Bias-temperature stability test for metal-oxide semiconductor field-effect transistors (MOSFET). Part 1: Fast BTI Test method.

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- ii) affects other national standard(s)
- iii) requires additional national guidance or information

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Introduction

This draft standard is based on national and international discussions. Your comments on this draft are invited and will assist in the preparation of the consequent standard.

For international standards, comments will be reviewed by the relevant UK national committee before sending the consensus UK vote and comments to the international committee, which will then decide appropriate action. If the international standard is approved, it is usual for the text to be published as a British Standard.

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UK Vote

Please indicate whether you consider the UK should submit a negative (with supporting technical reasons) or positive vote on this draft. Please indicate if you are aware of any reason why this draft standard should not be published as a British Standard.

Submission of Comments

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Template for comments and secretariat observations

Date: xx/xx/20xx	Document: ISO/DIS xxxx
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1	2	(3)	4	5	(6)	7
MB	Clause No./ Subclause No./Annex (e.g. 3.1)	Paragraph/Figure/ Table/Note	Type of comment	Commend (justification for change) by the MB	Proposed change by the MB	Secretariat observations on each comment submitted
	3.1	Definition 1	ed	Definition is ambiguous and needs clarifying.	Amend to read '...so that the mains connector to which no connection...'	
	6.4	Paragraph 2	te	The use of the UV photometer as an alternative cannot be supported as serious problems have been encountered in its use in the UK.	Delete reference to UV photometer.	



47/2442/CD

COMMITTEE DRAFT (CD)

PROJECT NUMBER:

IEC 62373-1 ED1

DATE OF CIRCULATION:

2017-11-17

CLOSING DATE FOR COMMENTS:

2018-02-09

SUPERSEDES DOCUMENTS:

47/2387/NP,47/2419/RVN

IEC TC 47 : SEMICONDUCTOR DEVICES

SECRETARIAT:

Korea, Republic of

SECRETARY:

Mr Cheolung Cha

OF INTEREST TO THE FOLLOWING COMMITTEES:

TC 91,TC 104

PROPOSED HORIZONTAL STANDARD:

☐

Other TC/SCs are requested to indicate their interest, if any, in this CD to the secretary.

FUNCTIONS CONCERNED:

☐ EMC

☐ ENVIRONMENT

☐ QUALITY ASSURANCE

☐ SAFETY

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Recipients of this document are invited to submit, with their comments, notification of any relevant patent rights of which they are aware and to provide supporting documentation.

TITLE:

Semiconductor devices – Bias-temperature stability test for metal-oxide semiconductor field-effect transistors (MOSFET) - Part 1: Fast BTI Test method

NOTE FROM TC/SC OFFICERS:

Agreed to circulate CD after preliminary check by experts during Regensburg meeting.

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SEMICONDUCTOR DEVICES –
Bias-temperature stability test for metal-oxide semiconductor field-effect
transistors (MOSFET) –****Part 1: Fast BTI Test method**

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The text of this International Standard is based on the following documents:

FDIS	Report on voting
XX/XX/FDIS	XX/XX/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.